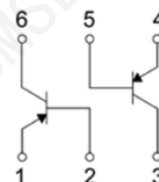
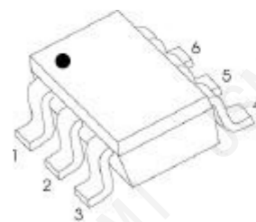


Features

- ◆ Two transistors in one package
- ◆ Reduces number of components and board space
- ◆ No mutual interference between the transistors



Equivalent Circuit

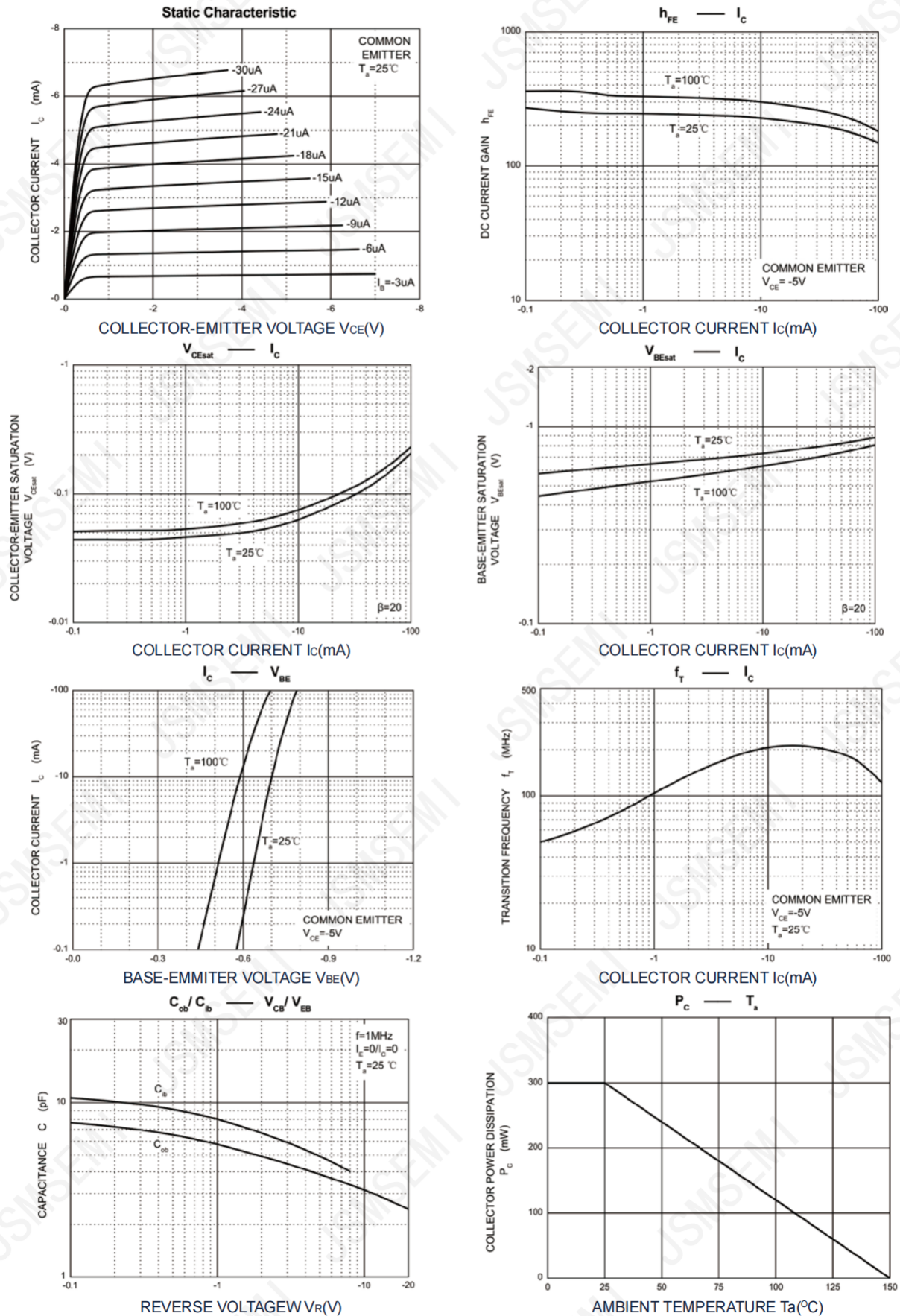
Absolute Maximum Ratings(TA=25℃)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	°C/W
T_J, T_{stg}	Operation Junction And Storage Temperature Range	-55 ~ +150	°C

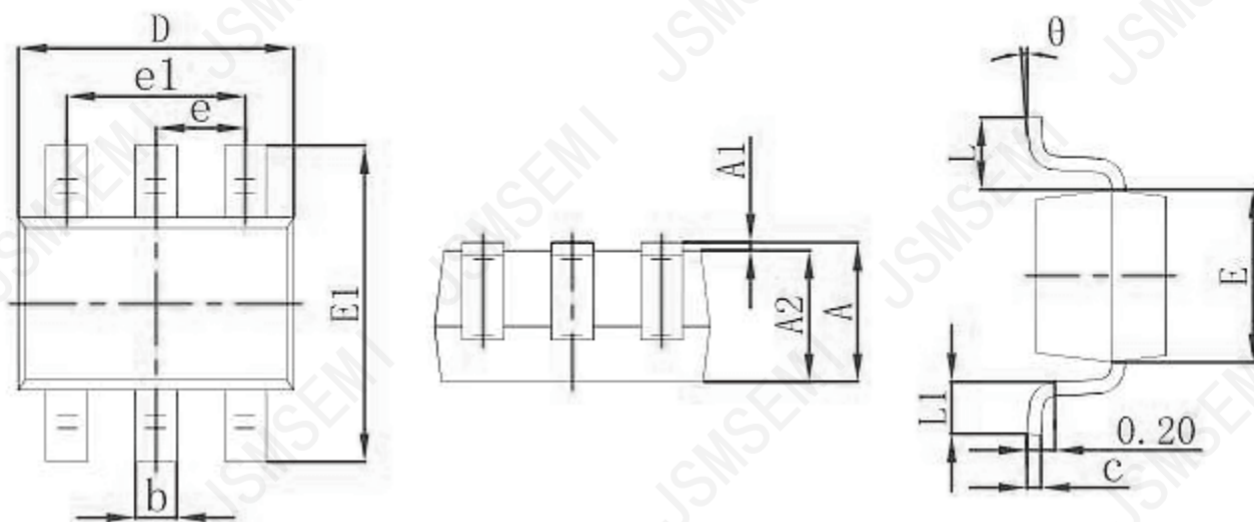
Electrical Characteristics (TA=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -10\mu A, I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA, I_B = 0$	-45			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -10\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -30V, I_E = 0$			-15	nA
h_{FE}	DC current gain	$V_{CE} = -5V, I_C = -2mA$	200		450	
$V_{CE(sat)(1)}$	Collector-emitter saturation voltage	$I_C = -10mA, I_B = -0.5mA$			-0.3	V
$V_{CE(sat)(2)}$		$I_C = -100mA, I_B = -5mA$			-0.65	V
$V_{BE(sat)(1)}$	Base-emitter saturation voltage	$V_{CE} = -5V, I_C = -2mA$	-0.6		-0.75	V
$V_{BE(sat)(2)}$		$V_{CE} = -5V, I_C = -10mA$			-0.82	V
f_T	Transition frequency	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$		200		MHz
C_{ob}	Base-emitter saturation voltage	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		3.5		pF
NF	Noise figure	$V_{CE} = -5V, I_C = -0.2mA, f = 1kHz, R_s = 2K\Omega, BW = 200Hz$		2.5		dB

Typical Characteristics



SOT-363 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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